



STU10NM65N Information



For Reference Only

Part Number STU10NM65N
Manufacturer STMicroelectronics

Category Discrete Semiconductor Products
Transistors - FETs, MOSFETs - Single

Description MOSFET N-CH 650V 9A IPAK

Package TO-251-3 Short Leads, IPak, TO-251AA

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



Request a Quote

Certified Quality

Heisener's commitment to quality has shaped our processes for sourcing, testing, shipping, and every step in between. This foundation underlies each component we sell.









STU10NM65N Specifications

Manufacturer Part Number STU10NM65N Manufacturer STMicroelectronics Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-251-3 Short Leads, IPak, TO-251AA Series MDmesh? II FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 650V Current - Continuous Drain (Id) @ 25°C 9A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4V @ 250µA Gate Charge (Qg) (Max) @ Vgs 25nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 850PF @ 50V Vgs (Max) ±25PF @ 50V Vgs (Max) 9W (Tc) Rds On (Max) @ Id, Vgs 480 mOhm @ 4.5A, 10V Operating Temperature 150°C (TJ) Mounting Type Through Hole Supplier Device Package I-Pak Package / Case TO-251-3 Short Leads, IPak, TO-251AA Report errors? Report errors?		
CategoryDiscrete Semiconductor ProductsTransistors - FETs, MOSFETs - SinglePackageTO-251-3 Short Leads, IPak, TO-251AASeriesMDmesh? IIFET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)650VCurrent - Continuous Drain (Id) @ 25°C9A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs25nC @ 10VInput Capacitance (Ciss) (Max) @ Vds850pF @ 50VVgs (Max)±25VFET Feature-Power Dissipation (Max)90W (Tc)Rds On (Max) @ Id, Vgs480 mOhm @ 4.5A, 10VOperating Temperature150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageI-PakPackage / CaseTO-251-3 Short Leads, IPak, TO-251AA	Manufacturer Part Number	STU10NM65N
Package TO-251-3 Short Leads, IPak, TO-251AA Series MDmesh? II FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 650V Current - Continuous Drain (Id) @ 25°C 9A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4V @ 250μA Gate Charge (Qg) (Max) @ Vgs 25nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 850pF @ 50V Vgs (Max) ±25V FET Feature - Power Dissipation (Max) 90W (Tc) Rds On (Max) @ Id, Vgs 480 mOhm @ 4.5A, 10V Operating Temperature 150°C (TJ) Mounting Type Through Hole Supplier Device Package I-Pak Package / Case TO-251-3 Short Leads, IPak, TO-251AA	Manufacturer	STMicroelectronics
PackageTO-251-3 Short Leads, IPak, TO-251AASeriesMDmesh? IIFET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)650VCurrent - Continuous Drain (Id) @ 25°C9A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs25nC @ 10VInput Capacitance (Ciss) (Max) @ Vds850pF @ 50VVgs (Max)±25VFET Feature-Power Dissipation (Max)90W (Tc)Rds On (Max) @ Id, Vgs480 mOhm @ 4.5A, 10VOperating Temperature150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageI-PakPackage / CaseTO-251-3 Short Leads, IPak, TO-251AA	Category	Discrete Semiconductor Products
Series MDmesh? II FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C 9A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4V @ 250µA Gate Charge (Qg) (Max) @ Vgs 25nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 850pF @ 50V Vgs (Max) ±25V FET Feature - Power Dissipation (Max) 90W (Tc) Rds On (Max) @ Id, Vgs 480 mOhm @ 4.5A, 10V Operating Temperature 150°C (TJ) Mounting Type Through Hole Supplier Device Package I-Pak Package / Case Toutone (Sine) (Package (Package) Package (Package) TO-251-3 Short Leads, IPak, TO-251AA		Transistors - FETs, MOSFETs - Single
FET Type Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C Prive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature Mounting Type Supplier Device Package Package / Case N-Channel 10V 9A (Tc) Rdv 250μA 850μF @ 50V 10V 850μF @ 50V 480 mOhm 4.5A, 10V 150°C (TJ) Mounting Type Through Hole 1-Pak Package / Case TO-251-3 Short Leads, IPak, TO-251AA	Package	TO-251-3 Short Leads, IPak, TO-251AA
Technology Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C Prive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) Vgs (Vgs (Vgs (Vgs (Vgs (Vgs (Vgs (Vgs (Series	MDmesh? II
Drain to Source Voltage (Vdss)650 VCurrent - Continuous Drain (Id) @ 25°C9A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs25nC @ 10VInput Capacitance (Ciss) (Max) @ Vds850pF @ 50VVgs (Max)±25VFET Feature-Power Dissipation (Max)90W (Tc)Rds On (Max) @ Id, Vgs480 mOhm @ 4.5A, 10VOperating Temperature150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageI-PakPackage / CaseTO-251-3 Short Leads, IPak, TO-251AA	FET Type	N-Channel
Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature Mounting Type Supplier Device Package Package / Case PA (Tc) 9A (Tc) 9A (Tc) 9A (Tc) 9A (Tc) 9A (Tc) 9A (Tc) 4V @ 250µA 850pF @ 50V 850pF @ 50V 90V 850pF @ 50V 480 mOhm @ 4.5A, 10V 150°C (TJ) Through Hole 150°C (TJ) Through Hole	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs25nC @ 10VInput Capacitance (Ciss) (Max) @ Vds850pF @ 50VVgs (Max)±25VFET Feature-Power Dissipation (Max)90W (Tc)Rds On (Max) @ Id, Vgs480 mOhm @ 4.5A, 10VOperating Temperature150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageI-PakPackage / CaseTO-251-3 Short Leads, IPak, TO-251AA	Drain to Source Voltage (Vdss)	650V
Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature Mounting Type Through Hole Supplier Device Package Package / Case 4V @ 250μA 4V @ 250μA 4S DQ (10V 850pF @ 50V 425V FET Feature - POW (Tc) 480 mOhm @ 4.5A, 10V 150°C (TJ) Through Hole 1-Pak TO-251-3 Short Leads, IPak, TO-251AA	Current - Continuous Drain (Id) @ 25°C	9A (Tc)
Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds 850pF @ 50V Vgs (Max) ±25V FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 480 mOhm @ 4.5A, 10V Operating Temperature 150°C (TJ) Mounting Type Through Hole Supplier Device Package I-Pak Package / Case TO-251-3 Short Leads, IPak, TO-251AA	Drive Voltage (Max Rds On, Min Rds On)	10V
Input Capacitance (Ciss) (Max) @ Vds 850pF @ 50V Vgs (Max) ±25V FET Feature - Power Dissipation (Max) 90W (Tc) Rds On (Max) @ Id, Vgs 480 mOhm @ 4.5A, 10V Operating Temperature 150°C (TJ) Mounting Type Through Hole Supplier Device Package I-Pak Package / Case TO-251-3 Short Leads, IPak, TO-251AA	Vgs(th) (Max) @ Id	4V @ 250μA
Vgs (Max) ±25V FET Feature - Power Dissipation (Max) 90W (Tc) Rds On (Max) @ Id, Vgs 480 mOhm @ 4.5A, 10V Operating Temperature 150°C (TJ) Mounting Type Through Hole Supplier Device Package I-Pak Package / Case TO-251-3 Short Leads, IPak, TO-251AA	Gate Charge (Qg) (Max) @ Vgs	25nC @ 10V
FET Feature - Power Dissipation (Max) 90W (Tc) Rds On (Max) @ Id, Vgs 480 mOhm @ 4.5A, 10V Operating Temperature 150°C (TJ) Mounting Type Through Hole Supplier Device Package I-Pak Package / Case TO-251-3 Short Leads, IPak, TO-251AA	Input Capacitance (Ciss) (Max) @ Vds	850pF @ 50V
Power Dissipation (Max) Rds On (Max) @ Id, Vgs 480 mOhm @ 4.5A, 10V Operating Temperature 150°C (TJ) Mounting Type Through Hole Supplier Device Package I-Pak Package / Case TO-251-3 Short Leads, IPak, TO-251AA	Vgs (Max)	±25V
Rds On (Max) @ Id, Vgs480 mOhm @ 4.5A, 10VOperating Temperature150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageI-PakPackage / CaseTO-251-3 Short Leads, IPak, TO-251AA	FET Feature	-
Operating Temperature 150°C (TJ) Mounting Type Through Hole Supplier Device Package I-Pak Package / Case TO-251-3 Short Leads, IPak, TO-251AA	Power Dissipation (Max)	90W (Tc)
Mounting Type Through Hole Supplier Device Package I-Pak Package / Case TO-251-3 Short Leads, IPak, TO-251AA	Rds On (Max) @ Id, Vgs	480 mOhm @ 4.5A, 10V
Supplier Device Package I-Pak Package / Case TO-251-3 Short Leads, IPak, TO-251AA	Operating Temperature	150°C (TJ)
Package / Case TO-251-3 Short Leads, IPak, TO-251AA	Mounting Type	Through Hole
	Supplier Device Package	I-Pak
Report errors?	Package / Case	TO-251-3 Short Leads, IPak, TO-251AA
		Report errors?

STU10NM65N Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

STU10NM65N Payment Methods



















STU10NM65N Shipping Methods













If you have any question about STU10NM65N, please do not hesitate to contact us!

Website: https://www.heisener.com E-mail: salesdept@heisener.com